

MOSFETs Silicon N-Channel MOS (DTMOSVI)

# **TK040Z65Z**

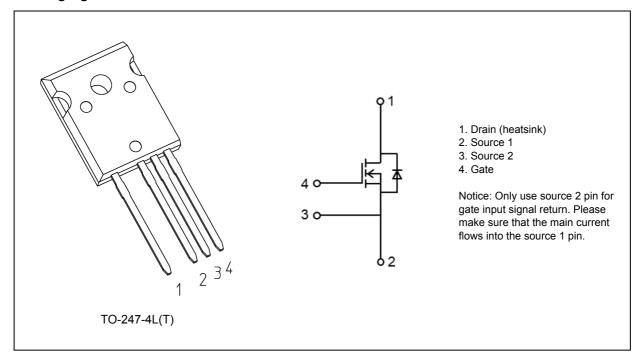
#### 1. Applications

· Switching Power Supplies

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.033 \Omega$  (typ.)
- (2) High-speed switching properties with lower capacitance.
- (3) Enhancement mode:  $V_{th} = 3$  to 4 V ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 2.85 \text{ mA}$ )

### 3. Packaging and Internal Circuit



Start of commercial production

Downloaded from Arrow.com.



## 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristics                | Symbol                  | Rating           | Unit       |       |
|--------------------------------|-------------------------|------------------|------------|-------|
| Drain-source voltage           |                         | $V_{DSS}$        | 650        | V     |
| Gate-source voltage            | ,                       | V <sub>GSS</sub> | ±30        |       |
| Drain current (DC)             | (Note 1)                | I <sub>D</sub>   | 57         | Α     |
| Drain current (pulsed)         | (Note 1)                | I <sub>DP</sub>  | 228        |       |
| Power dissipation (7           | Γ <sub>c</sub> = 25 °C) | $P_{D}$          | 360        | W     |
| Single-pulse avalanche energy  | (Note 2)                | E <sub>AS</sub>  | 702        | mJ    |
| Single-pulse avalanche current |                         | I <sub>AS</sub>  | 14.2       | Α     |
| Reverse drain current (DC)     | (Note 1)                | I <sub>DR</sub>  | 57         |       |
| Reverse drain current (pulsed) | (Note 1)                | I <sub>DRP</sub> | 228        |       |
| Channel temperature            |                         | T <sub>ch</sub>  | 150        | °C    |
| Storage temperature            |                         | T <sub>stg</sub> | -55 to 150 |       |
| Mounting torque                |                         | TOR              | 0.8        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max   | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance    |                       | 0.347 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 50    |      |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25 °C (initial), L = 6.16 mH,  $I_{AS}$  = 14.2 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур.  | Max  | Unit |
|--------------------------------|----------------------|---|-----|-------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _     | ±1   | μΑ   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V    | _   | _     | 2    |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 650 | _     | _    | V    |
| Gate threshold voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.85 mA  | 3   | _     | 4    |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 28.5 A   | _   | 0.033 | 0.04 | Ω    |

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                               | Symbol             | Test Condition  | Min | Тур. | Max | Unit |
|---|--------------------|---|-----|------|-----|------|
| Input capacitance                             | C <sub>iss</sub>   | V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 100 kHz | _   | 6250 | _   | pF   |
| Reverse transfer capacitance                  | C <sub>rss</sub>   |   | _   | 4    | _   |      |
| Output capacitance                            | C <sub>oss</sub>   |   | _   | 140  | _   |      |
| Effective output capacitance (energy related) | C <sub>o(er)</sub> | V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V         |     | 230  |     | pF   |
| Gate resistance                               | r <sub>g</sub>     | V <sub>DS</sub> = OPEN , f = 1 MHz                          | _   | 2    | _   | Ω    |
| Switching time (rise time)                    | t <sub>r</sub>     | See Figure 6.2.1  | _   | 30   | _   | ns   |
| Switching time (turn-on time)                 | t <sub>on</sub>    |   | _   | 75   | _   |      |
| Switching time (fall time)                    | t <sub>f</sub>     |   | _   | 5    | _   |      |
| Switching time (turn-off time)                | t <sub>off</sub>   |   | _   | 170  |     | ns   |
| MOSFET dv/dt ruggedness                       | dv/dt              | $V_{DS} \le V_{(BR)DSS}$ , $I_D \le 28.5 A$                 | 120 | _    |     | V/ns |

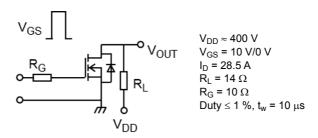


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$            | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 57 \text{ A}$ | _   | 105  |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |   | _   | 32   | _   |      |
| Gate-drain charge                               | $Q_{gd}$         |   |     | 27   |     |      |

# 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

| Characteristics               | Symbol          | Test Condition  | Min | Тур. | Max  | Unit |
|-------------------------------|-----------------|---|-----|------|------|------|
| Diode forward voltage         | $V_{DSF}$       | I <sub>DR</sub> = 57 A, V <sub>GS</sub> = 0 V                               | _   | _    | -1.7 | V    |
| Reverse recovery time         |                 | V <sub>DD</sub> = 400 V,  |     | 410  | _    | ns   |
| Reverse recovery charge       | $Q_{rr}$        | $I_{DR}$ = 28.5 A, $V_{GS}$ = 0 V $I_{DR}$ /dt = 100 A/ $\mu$ s             | _   | 8.0  | _    | μС   |
| Peak reverse recovery current | I <sub>rr</sub> | -αιρκ/αι – 100 Α/μδ   | _   | 39   | _    | Α    |
| Diode dv/dt ruggedness        | dv/dt           | $V_{DD} \le 400 \text{ V}, I_{DR} \le 28.5 \text{ A}, V_{GS} = 0 \text{ V}$ | 50  | _    | _    | V/ns |



## 7. Marking (Note)

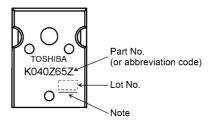


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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#### 8. Characteristics Curves (Note)

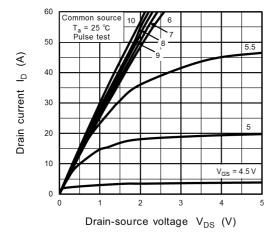
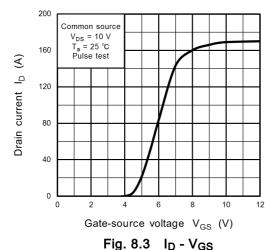
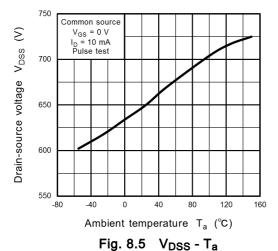


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>





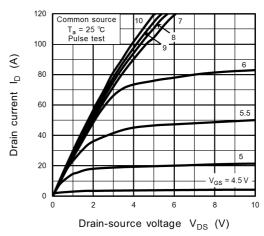


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

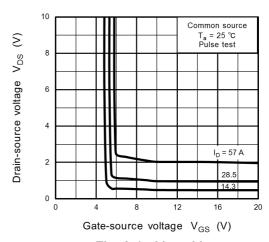


Fig. 8.4 VDS - VGS

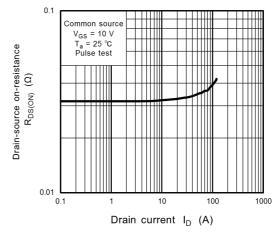


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>



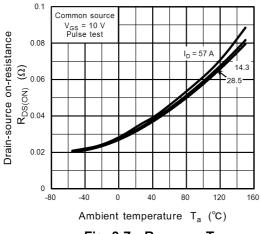


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

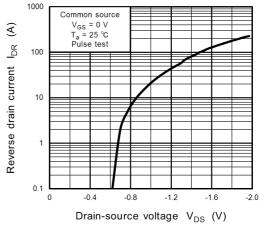


Fig. 8.8 IDR - VDS

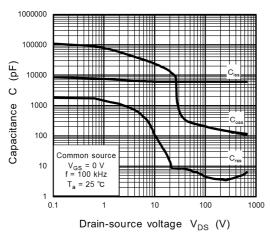


Fig. 8.9 C - V<sub>DS</sub>

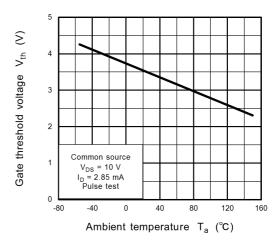


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

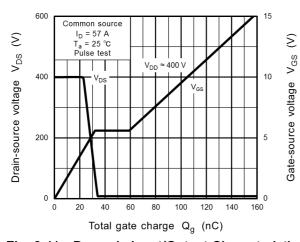


Fig. 8.11 Dynamic Input/Output Characteristics

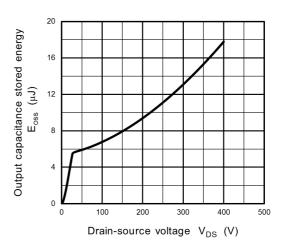


Fig. 8.12 E<sub>OSS</sub> - V<sub>DS</sub>



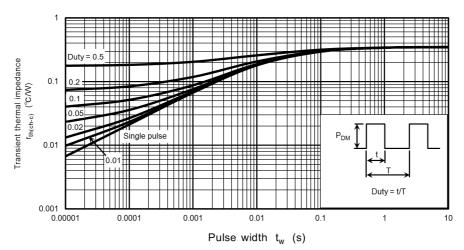


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

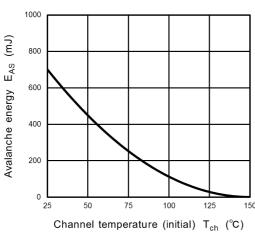


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

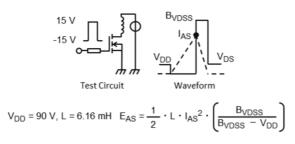


Fig. 8.16 Test Circuit/Waveform

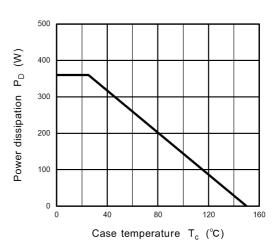


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

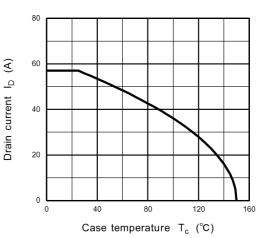


Fig. 8.17 I<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)



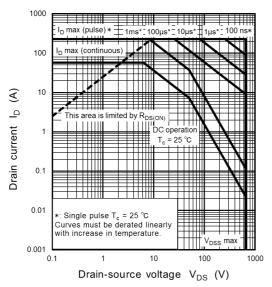


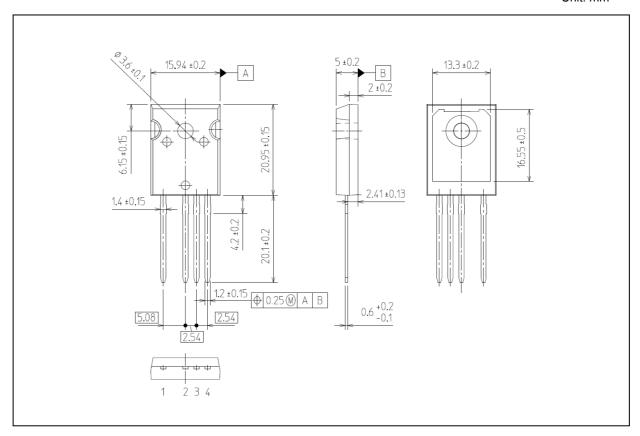
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 6.35 g (typ.)

| Package Name(s)        |  |  |
|------------------------|--|--|
| TOSHIBA: 2-16M2A       |  |  |
| Nickname: TO-247-4L(T) |  |  |



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